Central
Semiconductor Corp.
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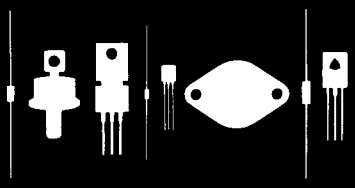
Hauppauge, New York 11788



MPS3392
MPS3393
MPS3394
MPS3395

NPN SILICON SIGNAL TRANSISTORS

JEDEC TO-92 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR MPS3392 Series types are Silicon NPN Transistors designed for small signal amplifier and low power audio applications.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNIT
Collector-Base Voltage	V_{CBO}	25	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector-Current	I_C	100	mA
Power Dissipation	P_D	625	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 TO +150	°C
Thermal Resistance	θ_{JA}	0.2	°C/mW

ELECTRICAL CHARACTERISTICS (T_A=25°C)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_{CBO}	V_{CB}=18V		0.1	μA
I_{EBO}	V_{EB}=5.0V		0.1	μA
BV_{CEO}	I_C=1.0mA	25		V
h_{FE}	V_{CE}=4.5V, I_C=2.0mA (MPS3392)	150	300	
h_{FE}	V_{CE}=4.5V, I_C=2.0mA (MPS3393)	90	180	
h_{FE}	V_{CE}=4.5V, I_C=2.0mA (MPS3394)	55	110	
h_{FE}	V_{CE}=4.5V, I_C=2.0mA (MPS3395)	150	500	
h_{fe}	V_{CE}=4.5V, I_C=2.0mA, f=1.0kHz (MPS3392)	150	500	
h_{fe}	V_{CE}=4.5V, I_C=2.0mA, f=1.0kHz (MPS3393)	90	400	
h_{fe}	V_{CE}=4.5V, I_C=2.0mA, f=1.0kHz (MPS3394)	55	300	
h_{fe}	V_{CE}=4.5V, I_C=2.0mA, f=1.0kHz (MPS3395)	150	800	
C_{ob}	V_{CB}=10V, f=1.0MHz		3.5	pF